



SINGLE BIT DUAL POWER SUPPLY TRANSLATING TRANSCEIVER WITH 3 STATE OUTPUTS

Description

The 74AVCH1T45 is a single bit, dual supply transceiver with 3-state outputs suitable for transmitting a single logic bit across different voltage domains. The 74AVCH1T45 is a variant of the 74AVC1T45 that includes a bus hold feature at each input. The A input/output pin is designed to track V_{CCA} while the B input/output tracks V_{CCB}. This arrangement allows for universal low-voltage translation between any voltages from 1.2V to 3.6V. The Direction pin (DIR) controls the direction of the transceiver and in a logic voltage related to V_{CCA}. When a high logic level is applied to DIR the A pin becomes an input and the B pin becomes the output. Conversely the roles of A and B are reversed when DIR is asserted low.

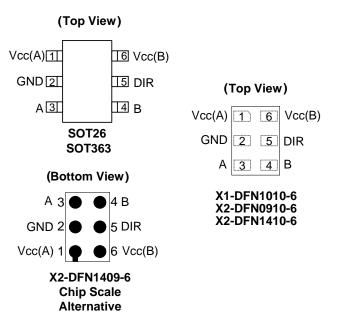
The 3-state feature occurs when either of the power supply voltages are zero. This is also an loff feature and allows for the output to remain in a high impedance state with both power supplies at 0V preventing damaging backflow currents and providing power down electrical isolation up to 3.6 V as not to interfere with any logic activity on pin A or B.

The bus hold feature maintains the previous logic level therefore a valid logic level is always present eliminating the need for additional resistors for an unused or disconnected inputs.

Features

- Wide Supply Voltage Range:
 - V_{CC}(A): from 1.2V to 3.6V
 - V_{CC}(B): from 1.2V to 3.6V
 - ± 12mA Output Drive at 3.3V
- High Noise Immunity (100mV hysteresis typical)
- IOFF Supports Partial-Power-Down Mode Operation
- I_{OFF} controlled by either V_{CC} being at 0V
- Inputs accept up to 4.6V
- ESD Protection Exceeds JESD 22
 - 200-V Machine Model (A115)
 - 2000-V Human Body Model (A114)
 - 1000 V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- X2-DFN1409-6 package designed as a direct replacement for chip scale packaging.
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Pin Assignments



Applications

- Voltage Level Translation: Well suited to join logic types operating at different voltages
- Power Down Signal Isolation: If either voltage domain is turned off the signal is isolated and there is no loading on signal lines
- Wide array of products such as:
 - Cell Phones, Tablets, E-Readers
 - PCs, Notebooks, Netbooks, Ultrabooks
 - Networking, Routers, Gateways
 - Computer Peripherals, Hard Drives, CD/DVD ROMs
 - TVs, DVDs, DVRs, Set Top Boxes
 - Personal Navigation / GPS
 - MP3 players, Cameras, Video Recorders

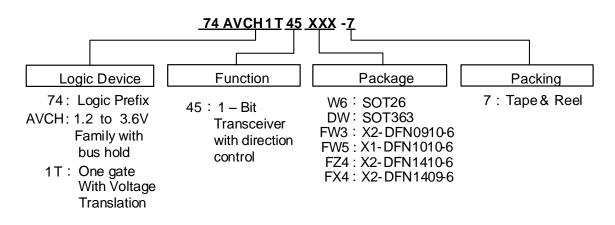
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Ordering Information



Part Number	Deekere Cede	Deelegring	7" Tape and	Reel (Note 7)
Part Number	Package Code	Packaging	Quantity	Part Number Suffix
74AVCH1T45W6-7	W6	SOT26	3,000/Tape & Reel	-7
74AVCH1T45DW-7	DW	SOT363	3,000/Tape & Reel	-7
74AVCH1T45FW3-7	FW3	X2-DFN0910-6	5,000/Tape & Reel	-7
74AVCH1T45FW5-7	FW5	X1-DFN1010-6	5,000/Tape & Reel	-7
74AVCH1T45FZ4-7	FZ4	X2-DFN1410-6	5,000/Tape & Reel	-7
74AVCH1T45FX4-7	FX4	X2-DFN1409-6	5,000/Tape & Reel	-7

Notes: 4. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf

Pin Descriptions

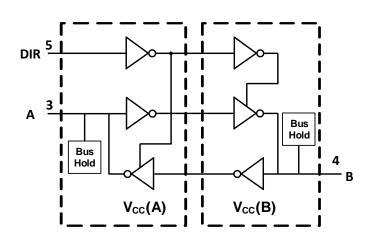
	D'	
Pin Name	Pin	Function
VCC(A)	1	Supply for I/O pin A and reference for DIR
GND	2	Ground
A	3	Data Input/Output
В	4	Data Input/Output
DIR	5	Direction Control
VCC(B)	6	Supply for I/O pin B

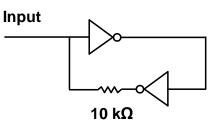
Function Table

Supply voltage	Input	Input/Output			
V _{CC(A)} , V _{CC(B)}	DIR (Direction Pin)	Α	В		
1.2 V to 3. 6 V	L	A=B	input		
1.2 V to 3. 6 V	Н	input	B=A		
GND	Х	Z	Z		



Logic Diagram





Bus Hold Circuit Previous Input is Latched Input Signals must be strong enough to override 10kΩ

Symbol	Parameter		Rating	Unit			
ESD HBM	Human Body Model ESD Protection		2	kV			
ESD CDM	Charged Device Model ESD Protection		1	kV			
ESD MM	Machine Model ESD Protection		200	V			
V _{CC} (A), V _{CC} (B)	Supply Voltage Range						
VI	Input Voltage Range						
Vo	Voltage Applied to Output in High Impedance or IOFF	-0.5 to +4.6	V				
	Valtage Applied to Output in Llighten Levy State	A pin	-0.5 to V _{CC} (A) +0.5	V			
Vo	Voltage Applied to Output in High or Low State	B pin	-0.5 to V _{CC} (B) +0.5	V			
I _{IK}	Input Clamp Current V _I <0		-50	mA			
I _{ОК}	Output Clamp Current		-50	mA			
lo	Continuous Output Current		±50	mA			
	Continuous Current Through V _{CC} or GND	•					
TJ	Operating Junction Temperature		-40 to +150	°C			
T _{STG}	Storage Temperature		-65 to +150	°C			

Absolute Maximum Ratings (Note 5) (@T_A = +25°C, unless otherwise specified.)

Note: 5. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



Recommended Operating Condition (Notes 6, 7 & 8) (@T_A = +25°C, unless otherwise specified.)

Symbol	Para	meter	V _{CCI}	Vcco	Min	Max	Units	
V _{CC} (A)	Operating Volta	ige	_	_	1.2	3.6	V	
V _{CC} (B)	Operating Volta	ige	_	—	1.2	3.6	V	
			1.2 to 1.95V	1.2 to 3.6V	0.65 x V _{CC(A)}	—		
V _{IH}	High-Level Input Voltage	Data Inputs	1.95 to 2.7V	1.2 to 3.6V	1.6	_	V	
	input voltage		2.7V to 3.6V	1.2 to 3.6V	2	_		
			1.2 to 1.95V	1.2 to 3.6V	_	0.35 x V _{CC(A)}		
VIL	Low-Level Input Voltage	Data Inputs	1.95 to 2.7V	1.2 to 3.6V	_	0.7	V	
	mput voltago		2.7V to 3.6V	1.2 to 3.6V	—	0.8		
		DIR	1.2 to 1.95V	1.2 to 3.6V	0.65 x V _{CC(B)}	—		
V _{IH}	High-Level Input Voltage	vel $(referenced to 1.95 to 2.7)/(1.2 to 3.6)/(1.6)$		1.6	—	V		
	mpar renage	V _{CCA})	2.7 to 3.6V	1.2 to 3.6V	2	_		
		DIR	1.2 to 1.95V	1.2 to 3.6V	—	0.35 x V _{CC(B)}		
V _{IL} Low-Level Input Voltage	(referenced to	1.95 to 2.7V	1.2 to 3.6V	_	0.7	V		
	input voltage	V _{CCA})	2.7 to 3.6V	1.2 to 3.6V	_	0.8		
VI	Input Voltage		_	_	0	3.6	V	
N/		Active state	_	_	0	Vcco	V	
Vo	Output Voltage	3-state	—	—	0	3.6	V	
			1.2 to 3.6V	1.2V	_	-3		
			1.2 to 3.6V	1.4 to 1.6V	_	-6		
Іон	High-Level Outp	put Current	1.2 to 3.6V	1.65 to 1.95V	_	-8	mA	
			1.2 to 3.6V	2.3 to 2.7V	_	-9		
			1.2 to 3.6V	3 to 3.6V	_	-12		
			1.2 to 3.6V	1.2V	_	3		
			1.2 to 3.6V	1.4 to 1.6V	_	6		
IOL	Low-Level Output Current		1.2 to 3.6V	1.65 to 1.95V	_	8	mA	
		F	1.2 to 3.6V	2.3 to 2.7V	_	9		
		F	1.2 to 3.6V	3 to 3.6V	_	12		
Δt/ΔV	Input Transition Rate	Rise or Fall	1.2 to 3.6V	1.2 to 3.6V	_	5	ns/V	
TA	Operating Free	Air Temperature			-40	+85	°C	

Note:

6. V_{CCO} is the V_{CC} associated with the output port.

7. $V_{\mbox{CCI}}$ is the $V_{\mbox{CC}}$ associated with the input port.

8. All unused inputs of the device must be held at $V_{\mbox{CCI}}$ of GND.



0	Barrantan	-		N (A))/ (D)	Т	_A = +25°	С	T _A = -40°C	to +85°C	
Symbol	Parameter	I	est Conditions	V _{CC} (A)	V _{CC} (B)	Min	Тур	Max	Min	Max	Unit
		I _{OH} = -1	00µA	1.2 to 3.6V	1.2V to 3.6V	_	_		$V_{CC} - 0.2$	_	
		I _{OH} = -3	втА	1.2V	1.2V	_	0.95	_	_	_	
V	High Level	I _{OH} = -6	imA	1.4V	1.4V	—		_	1.05	—	V
V _{OH}	Output Voltage	I _{OH} = -8	mA	1.65V	1.65V	—	1	_	1.2	_	V
		I _{OH} = -9	ImA	2.3V	2.3V	—	_	_	1.75	—	
		I _{OH} = -1	2mA	3V	3V	—	_	_	2.3	—	
		I _{OL} = 10	00μΑ	1.2 to 3.6V	1.2V to 3.6V	_		_	_	0.2	
		$I_{OL} = 3r$	nA	1.2V	1.2V	—	0.15	_	—	—	
Max	Low-Level Output	$I_{OL} = 6r$	nA	1.4V	1.4V	_		_	—	0.35	v
V _{OL}	Voltage	$I_{OL} = 8r$	nA	1.65V	1.65V	_		_	_	0.45	V
		$I_{OL} = 9r$	nA	2.3V	2.3V	_	I	_	_	0.55	
		I _{OL} = 12	2mA	3V	3V	_		_	_	0.7	
lı	Input Current	DIR	$V_I = V_{CC}(A)$ or GND	1.2 to 3.6V	1.2 to 3.6V	-0.25	±0.25	0.25	-1	1	μA
I _{OFF}	Power Down	A Pin	V_1 or $V_0 = 0$ to 3.6V	0V	0 to 3.6V	-1	±0.1	1	-5	5	μA
011	Leakage Current	B Pin		0 to 3.6V	0	-1	±0.1	1	-5	5	
	3-State Leakage	B Pin	$V_0 = V_{CCO}$ or Gnd	0V	0 to 3.6V	-2.5	±0.5	2.5	-5	5	
loz	Current	A Pin	V _I = V _{CCI} or Gnd	0 to 3.6V	0	-2.5	±0.5	2.5	-5	5	μA
				1.2 to 3.6V	11.2 to 3.6V	_	_		_	10	
ICCA	Supply Current		_{CI} or GND	3.6V	0V	_		_	_	-2	μA
		$I_0 = 0$		0V	3.6V	_		_	_	10	
		., .,	0.115	1.2 to 3.6V	1.2 to 3.6V	_			_	10	
I _{CCB}	Supply Current	-	_{CI} or GND	0V	3.6V	_			_	10	μA
		I _O = 0		3.6V	0V	_	_	_	_	-2	
I _{CCA} + I _{CCB}	Supply Current	$V_I = V_C$ $I_O = 0$	_{CI} or GND	1.2 to 3.6V	1.2 to 3.6V	_	_	_	_	20	μA
CI	Input Capacitance	DIR	V _I = V _{CC} (A) or GND	3.3V	3.3V	_	2.5		_	_	pF
CIO	Input/Output Capacitance	A or B pin	V _I = V _{CC} (A)/(B) or GND	3.3V	3.3V	_	6.0	_	_	_	pF

Electrical Characteristics (Notes 9 & 10) (@T_A = +40°C to +85°C, unless otherwise specified.)

Notes: 9. V_{CCO} is the V_{CC} associated with the output port.

10. V_{CCI} is the V_{CC} associated with the input port.



Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
		SOT26		_	166	_	
		SOT363		_	371	_	
0	Thermal Resistance Junction-	X2-DFN0910-6	(Note 11)	_	530	_	°C/W
θ_{JA}	to-Ambient	X2- DFN1410-6	(Note 11)	_	430	—	C/VV
		X2-DFN1409-6	-	_	450	_	
		X1-DFN1010-6			510	_	
		SOT26		_	46	—	
		SOT363			143	—	
0	Thermal Resistance Junction-	X2-DFN0910-6	(Nata 11)	_	260	_	8 0 AA
θ _{JC}	to-Case	X2- DFN1410-6	(Note 11)	_	190	_	°C/W
		X2-DFN1409-6			200	—	
		X1-DFN1010-6			250	_	

Note: 11. Test condition for all packages: Device mounted on FR-4 substrate PC board, 2oz copper with minimum recommended pad layout.

Switching Characteristics

Parameter	From (Input)	To (Output)	V _{CC} (B) = 1.2V	V _{CC} (B) = 1.5V ±0.1	V _{CC} (B) = 1.8V ±0.15V	V _{CC} (B) = 2.5V ±0.2V	V _{CC} (B) = 3.3V ±0.3V	Unit	
	(input)	(Output)	TYP	TYP	TYP	TYP	TYP		
t _{PLH}	А	В	3.3	2.7	2.4	2.3	2.4	ns	
t PHL	A	Б	3.3	2.7	2.4	2.3	2.4	115	
t _{PLH}	в	А	3.3	3.1	2.9	2.8	2.7	ns	
t _{PHL}	Ь	~	3.3	3.1	2.9	2.8	2.7		
t PHZ	DIR	А	5.1	5.2	5.3	5.2	3.7	ns	
t _{PLZ}	DIK	~	5.1	5.2	5.3	5.2	3.7	115	
t _{PHZ}	DIR	В	5.3	4.3	4.0	3.3	3.7	ns	
t _{PLZ}	DIK	Ь	5.3	4.3	4.0	3.3	3.7	115	
t _{PZH} *	DIR	А	8.6	7.3	6.8	6.1	6.4	ns	
t _{PZL} *	DIK	A	8.6	7.3	6.8	6.1	6.4	115	
t _{PZH} *	DIR	В	8.3	7.8	7.7	7.5	5.8	ns	
t _{PZL} *		6	8.3 7.8		7.7	7.5	5.8		

*Enable times are calculated vales see table at end of switching characteristics.

 V_{CC} (A) = 1.5V ± 0.1V, T_A = -40°C to +85°C, See Figure 1

Parameter	From (Input)	To (Output)	V _{CC} (B) = 1.2V		= 1.5V).1) = 1.8V 15V		= 2.5V .2V) = 3.3V .3V	Unit
	(input)	(Output)	TYP	Min	Max	Min	Max	Min	Max	Min	Max	
t _{PLH}	A	В	2.9	0.7	5.6	0.6	5.2	0.5	4.2	0.5	3.8	ns
t _{PHL}	~	Б	2.9	0.7	5.6	0.6	5.2	0.5	4.2	0.5	3.8	115
t _{PLH}	в	А	2.6	0.6	5.5	0.4	5.3	0.3	4.9	0.3	4.8	ns
t _{PHL}	Ь	A	2.6	0.6	5.5	0.4	5.3	0.3	4.9	0.3	4.8	115
t _{PHZ}	DIR	А	3.8	1.6	6.7	1.5	6.8	0.3	6.9	0.9	6.9	ns
t _{PLZ}	DIK	~	3.8	1.6	6.7	1.5	6.8	0.3	6.9	0.9	6.9	115
t _{PHZ}	DIR	в	5.1	1.8	8.1	1.6	7.1	1.1	4.7	1.4	4.5	ns
t _{PLZ}	DIK	Б	5.1	1.8	8.1	1.6	7.1	1.1	4.7	1.4	4.5	115
t _{PZH} *	DIR	А	7.7		13.6	_	12.4	—	9.6	—	9.3	ns
t _{PZL} *	DIK	A	7.7		13.6	_	12.4	—	9.6	—	9.3	115
t _{PZH} *	DIR	В	6.7	_	12.3	_	12	—	11.1	—	10.7	20
t _{PZL} *	DIR	В	6.7	_	12.3	_	12	_	11.1	_	10.7	ns

*Enable times are calculated vales see table at end of switching characteristics.



Switching Characteristics (Continued)

Parameter	From	To	V _{CC} (B) = 1.2V) = 1.5V 0.1		= 1.8V 15V		= 2.5V .2V		= 3.3V .3V	Unit	
	(Input)	(Output)	(Output)	TYP	Min	Max	Min	Max	Min	Max	Min	Max	
t _{PLH}	A	В	2.7	0.6	5.3	0.5	5.0	0.4	3.9	0.4	3.4	ns	
t _{PHL}	~	Б	2.7	0.6	5.3	0.5	5.0	0.4	3.9	0.4	3.4	115	
t _{PLH}	в	А	2.3	0.5	5.2	0.4	5.0	0.3	4.6	0.2	4.4	ns	
t _{PHL}	Б	A	2.3	0.5	5.2	0.4	5.0	0.3	4.6	0.2	4.4	115	
t _{PHZ}	DIR	А	3.8	1.6	5.9	1.6	5.9	1.6	5.9	0.5	6.0	ns	
t _{PLZ}	DIK	~	3.8	1.6	5.9	1.6	5.9	1.6	5.9	0.5	6.0	115	
t _{PHZ}	DIR	В	5.0	1.8	7.7	1.4	6.8	1.0	4.4	1.4	5.3	ns	
t _{PLZ}	DIK	Б	5.0	1.8	7.7	1.4	6.8	1.0	4.4	1.4	5.3	115	
t _{PZH} *	DIR	^	7.3	_	12.9		11.8	—	9.0	—	8.7	20	
t _{PZL} *	DIR	A	7.3	_	12.9		11.8	—	9.0	_	8.7	ns	
t _{PZH} *	DIR	В	6.5	_	11.2		10.9	—	9.8	_	9.4	20	
t _{PZL} *	UIK	Б	6.5	_	11.2	_	10.9	_	9.8	_	9.4	ns	

*Enable times are calculated vales see table at end of switching characteristics.

V_{CC} (A) = 2.5V \pm 0.2V, T_A = -40°C to +85°C, See Figure 1

Parameter	From (Input)	To (Output)	V _{CC} (B) = 1.2V		= 1.5V 0.1) = 1.8V 15V		= 2.5V .2V		= 3.3V .3V	Unit																																
	(input)	(Output)	TYP	Min	Max	Min	Max	Min	Max	Min	Max																																	
t _{PLH}	Α	В	2.6	0.5	4.9	0.4	4.6	0.3	3.4	0.3	3.0	20																																
t _{PHL}	A	Б	2.6	0.5	4.9	0.4	4.6	0.3	3.4	0.3	3.0	ns																																
t _{PLH}	В	А	2.2	0.4	4.2	0.3	3.8	0.2	3.4	0.2	3.3	ns																																
t _{PHL}	Б	A	2.2	0.4	4.2	0.3	3.8	0.2	3.4	0.2	3.3	115																																
t _{PHZ}	DIR	А	2.8	0.3	3.8	0.8	3.8	0.4	3.8	0.5	3.8	20																																
t _{PLZ}	DIK	A	2.8	0.3	3.8	0.8	3.8	0.4	3.8	0.5	3.8	ns																																
t _{PHZ}	DIR	В	4.9	2.0	7.6	1.5	6.5	0.6	4.1	1.0	4.0																																	
t _{PLZ}	DIR	Б	4.9	2.0	7.6	1.5	6.5	0.6	4.1	1.0	4.0	ns																																
t _{PZH} *	DIR	^	7.1	_	11.8	_	10.3	_	7.5	_	7.3	20																																
t _{PZL} *	DIK	А	A	A	A	A	A	A	A	A	A	A	A	A	A	A	A –	A	A	A	A	A	A	A	A	A	A	A	A	A	A	A	Α –	Α	7.1	_	11.8	_	10.3	_	7.5	_	7.3	ns
t _{PZH} *	DIP	В	5.4	_	8.6	_	8.1	—	7.0	—	6.6	20																																
t _{PZL} *	DIR	В	5.4	_	8.6	_	8.1	_	7.0	—	6.6	ns																																

*Enable times are calculated vales see table at end of switching characteristics.

V_{CC} (A) = 3.3V \pm 0.3V, T_{A} = -40°C to +85°C, See Figure 1

Parameter	From (Input)	-	From (Input)	To (Output)	V _{CC} (B) = 1.2V	V _{CC} (B) ±	= 1.5V 0.1) = 1.8V 15V		= 2.5V .2V		= 3.3V .3V	Unit
	(input)	(Output)	TYP	Min	Max	Min	Max	Min	Max	Min	Max			
t _{PLH}	А	В	2.6	0.4	4.7	0.3	4.4	0.2	3.3	0.2	2.8	20		
t _{PHL}	А	Б	2.6	0.4	4.7	0.3	4.4	0.2	3.3	0.2	2.8	ns		
tPLH	В	^	2.2	0.4	3.8	0.3	3.4	0.2	3	0.1	2.8			
t _{PHL}	D	A	2.2	0.4	3.8	0.3	3.4	0.2	3	0.1	2.8	ns		
t _{PHZ}	DIR	^	3.1	1.3	4.3	1.3	4.3	1.3	4.3	1.3	4.3			
t _{PLZ}		A	3.1	1.3	4.3	1.3	4.3	1.3	4.3	1.3	4.3	ns		
t _{PHZ}	DIR	В	4	0.7	7.4	0.6	6.5	0.7	4	1.5	4.9	20		
t _{PLZ}	DIK	Б	4	0.7	7.4	0.6	6.5	0.7	4	1.5	4.9	ns		
t _{PZH} *	DIR	^	6.2	_	11.2	_	9.9	_	7	_	6.7			
t _{PZL} *	DIR	A	6.2	_	11.2	_	9.9	—	7	_	6.7	ns		
t _{PZH} *	חוח	В	5.7	_	8.9	_	8.5	_	7.2	_	6.8			
t _{PZL} *	DIR	В	5.7	_	8.9	_	8.5	—	7.2	_	6.8	ns		

*Enable times are calculated vales see table at end of switching characteristics.



Enable Time Calculations

Enable times can be calculated as follows:

- t_{PZH} (DIR to A) = t_{PLZ} (DIR to B) + t_{PLH} (B to A)
- t_{PZL} (DIR to A) = t_{PHZ} (DIR to B) + t_{PHL} (B to A)
- t_{PZH} (DIR to B) = t_{PLZ} (DIR to A) + t_{PLH} (A to B)
- t_{PZL} (DIR to B) = t_{PHZ} (DIR to A) + t_{PHL} (A to B)

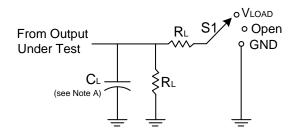
These times represent the length of time from a direction change plus the propagation time through the part. A new input signal should not be applied until the new input pin has been disabled.

Operating Characteristics (T_A = +25°C, unless otherwise specified.)

Parameter Power Dissipation Capacitance		Test Conditions	V _{CC} (A) = V _{CC} (B) = 1.8V Typ	V _{CC} (A) = V _{CC} (B) = 2.5V Typ	V _{CC} (A) = V _{CC} (B) = 3.3V Typ	V _{CC} (A) = V _{CC} (B) = 5V Typ	Unit
	A- input, B- output	$C_L = 0 pF$	3	4	4	4	
C _{PD} (A)	B- input, A- output	f = 10 MHz tr = tf = 1 ns	18	19	20	21	pF
	A- input, B- output	$C_L = 0 pF$	18	19	20	21	
C _{PD} (B)	B- input, A- output	f = 10 MHz tr = tf = 1 ns	3	4	4	4	pF

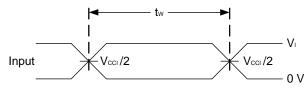


Parameter Measurement Information

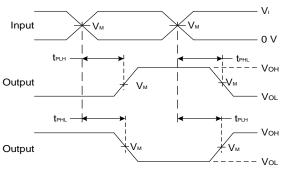


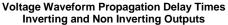
TEST	S1
t _{PLH} /t _{PHL}	Open
tplz/tpzl	Vload
t _{PHZ} /t _{PZH}	GND

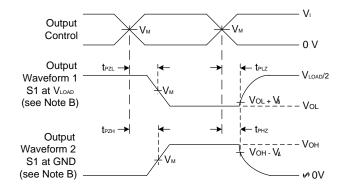
N ₂ ,2	Inputs		N _e .	N	C	D.	MA
Vcc	VI	t _R /t _F	VM	V _{LOAD}	C∟	R∟	VΔ
1.2V	Vcci	≤2ns	V _{CCO} /2	2 x V _{CCO}	15pF	2ΚΩ	0.15V
1.8V±0.15V	V _{CCI}	≤2ns	V _{CCO} /2	2 x V _{CCO}	15pF	2ΚΩ	0.15V
2.5V±0.2V	Vcci	≤2ns	V _{CCO} /2	2 x V _{CCO}	15pF	2ΚΩ	0.15V
3.3V±0.3V	V _{CCI}	≤2.5ns	V _{CCO} /2	2 x V _{CCO}	15pF	2ΚΩ	0.3V



Voltage Waveform Pulse Duration







Voltage Waveform Enable and Disable Times Low and High Level Enabling

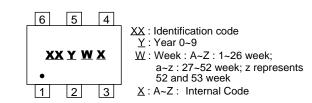
Figure 1 Load Circuit and Voltage Waveforms

- Notes: A. Includes test lead and test apparatus capacitance.
 - B. Waveform 1 is for an output with input set up as a low and device coming out or into 3-state via DIR control. Waveform 2 is for an output with input set up as a high and device coming out or into 3-state via DIR control.
 - C. All pulses are supplied at pulse repetition rate \leq 10 MHz.
 - D. t_{PLZ} and t_{PHZ} are the same as t_{DIS.}
 - E. t_{PZL} and t_{PZH} are the same as t_{EN} .
 - F. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$
 - G. V_{CCI} is the V_{CC} associated with the input.
 - F. V_{CCO} is the V_{CC} associated with the output.



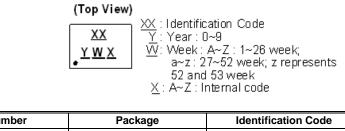
Marking Information

(1) SOT26, SOT363



Part Number	Package	Identification Code
74AVCH1T45W6-7	SOT26	VT
74AVCH1T45DW-7	SOT363	VR

(2) X2-DFN0910-6, X2-DFN1010-6, X2-DFN1410-6, and X2-DFN1409-6



Part Number	Package	Identification Code
74AVCH1T45FW3-7	X2-DFN0910-6	ZR
74AVCH1T45FW5-7	X1-DFN1010-6	VR
74AVCH1T45FX4-7	X2-DFN1409-6	VT
74AVCH1T45FZ4-7	X2-DFN1410-6	VS



Тур

0.05

1.10

0.75

0.38

0.15

3.00

0.95

1.<u>9</u>0

2.80

1.60

0.40 8°

7°

1.30

0.80

0.50

3.10

-

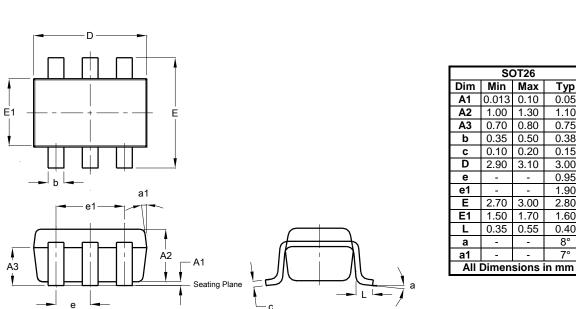
3.00

1.70

0.55

Package Outline Dimensions

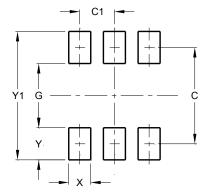
Please see http://www.diodes.com/package-outlines.html for the latest version.



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26

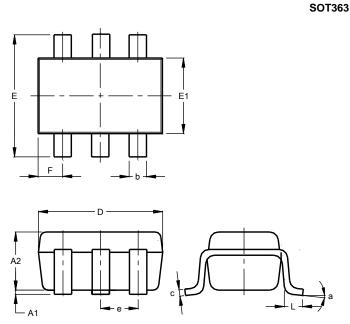


Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



Package Outline Dimensions (Cont.)

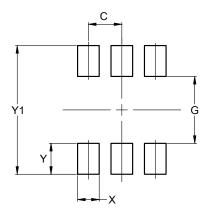
Please see http://www.diodes.com/package-outlines.html for the latest version.



c								
SOT363								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	1.00					
b	0.10	0.30	0.25					
С	0.10	0.22	0.11					
D	1.80	2.20	2.15					
E	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C).650 E	SC					
F	0.40	0.45	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All	Dimen	sions	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



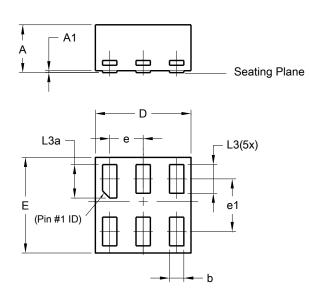
SOT363

Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500



Package Outline Dimensions

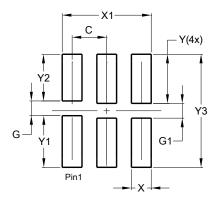
Please see http://www.diodes.com/package-outlines.html for the latest version.



	X1-DFN1010-6 (Type B)					
Dim	m Min Max Typ					
Α	-	0.50	0.39			
A1	-	0.04	-			
b	0.12	0.20	0.15			
D	0.95	1.050	1.00			
E	0.95	1.050	1.00			
е		0.35 B	SC			
e1		0.55 B	SC			
L3	0.27 0.30 0.30					
L3a	0.32	0.40	0.35			
All	Dimen	sions	in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



X1-DFN1010-6 (Type B)

X1-DFN1010-6 (Type B)

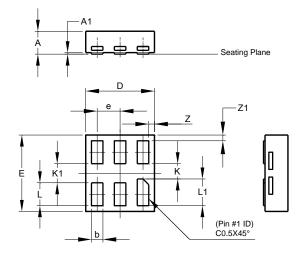
Dimensions	Value
Dimensions	(in mm)
С	0.350
G	0.150
G1	0.150
Х	0.200
X1	0.900
Y	0.500
Y1	0.525
Y2	0.475
Y3	1.150



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

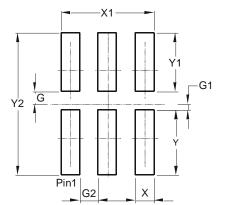




)	X2-DFN0910-6						
Dim	Min	Max	Тур				
Α	-	0.35	0.30				
A1	0	0.03	0.02				
b	0.10	0.20	0.15				
D	0.85	0.95	0.90				
E	0.95	1.05	1.00				
е	-	-	0.30				
K	0.20	-	-				
K1	0.25	-	-				
L	0.25	0.35	0.30				
L1	0.30	0.40	0.35				
Z	-	-	0.075				
Z1	-	-	0.075				
All D	imensi	ons in r	nm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN0910-6

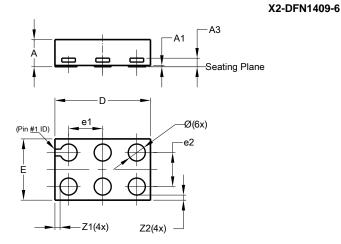
Dimensions	Value (in mm)
G	0.100
G1	0.050
G2	0.150
Х	0.150
X1	0.750
Ý	0.525
Y1	0.475
Y2	1.150

74AVCH1T45 Document number: DS40288 Rev. 1 - 2



Package Outline Dimensions (Cont.)

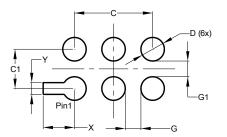
Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN1409-6				
Dim	Min	Max	Тур	
Α	-	0.40	0.39	
A1	0	0.05	0.02	
A3	-	-	0.13	
Ø	0.20	0.30	0.25	
D	1.35	1.45	1.40	
Е	0.85	0.95	0.90	
e1	-	-	0.50	
e2	-	-	0.50	
Z1	-	-	0.075	
Z2	-	-	0.075	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
Х	0.400

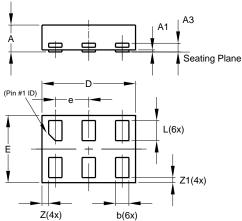
0.150

X2-DFN1409-6



Package Outline Dimensions (Cont.)

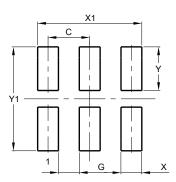
Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN1410-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3		_	0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
E	0.95	1.05	1.00	
е	_	_	0.50	
L	0.25	0.35	0.30	
Z			0.10	
Z1	0.045	0.105	0.075	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN1410-6

Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Y	0.525
Y1	1.250

X2-DFN1410-6



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2017, Diodes Incorporated

www.diodes.com

单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))